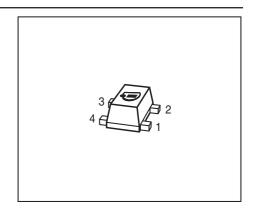


Low Noise Silicon Bipolar RF Transistor

- For ESD protected high gain low noise amplifier
- Excellent ESD performance typical value 1000 V (HBM)
- Outstanding G_{ms} = 20 dB
 Minimum noise figure NF_{min} = 0.9 dB
- Pb-free (ROHS compliant) and halogen-free thin small flat package with visible leads
- Qualification report according to AEC-Q101 available







ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration					Package	
BFP540FESD	AUs	1=B	2=E	3=C	4=E	-	-	TSFP-4

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{\sf CEO}$		V
<i>T</i> _A = 25 °C		4.5	
_T _A = -55 °C		4	
Collector-emitter voltage	V_{CES}	10	
Collector-base voltage	V_{CBO}	10	
Emitter-base voltage	V _{EBO}	1	
Collector current	$I_{\mathbb{C}}$	80	mA
Base current	l _B	8	
Total power dissipation ¹⁾	P _{tot}	250	mW
_ <i>T</i> _S ≤ 80 °C			
Junction temperature	T_{J}	150	°C
Storage temperature	T_{Stg}	-55 150	

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 $^{{}^1}T_{\rm S}$ is measured on the emitter lead at the soldering point to the pcb



Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	280	K/W

Electrical Characteristics at $T_{\rm A}$ = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	•	•	•		•
Collector-emitter breakdown voltage	V _{(BR)CEO}	4.5	5	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0	, ,				
Collector-emitter cutoff current	I _{CES}	-	-	10	μA
$V_{CE} = 10 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB} = 5 \text{V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	10	μΑ
$V_{\rm EB} = 0.5 \rm V, I_{\rm C} = 0$					
DC current gain	h _{FE}	50	110	170	_
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 3.5 V, pulse measured					

 $^{^{1}}$ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
AC Characteristics (verified by random sampling)						
Transition frequency	f _T	21	30	-	GHz	
$I_{\rm C}$ = 50 mA, $V_{\rm CE}$ = 4 V, f = 1 GHz						
Collector-base capacitance	C _{cb}	-	0.16	0.26	pF	
$V_{\text{CB}} = 2 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,						
emitter grounded						
Collector emitter capacitance	C _{ce}	-	0.4	-		
$V_{CE} = 2 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,						
base grounded						
Emitter-base capacitance	C _{eb}	-	0.55	-		
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,						
collector grounded						
Minimum noise figure	<i>NF</i> _{min}				dB	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 2 V, f = 1.8 GHz, $Z_{\rm S}$ = $Z_{\rm Sopt}$		-	0.9	1.4		
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 2 V, f = 3 GHz, $Z_{\rm S}$ = $Z_{\rm Sopt}$		-	1.3	-		
Power gain, maximum stable ¹⁾	G _{ms}	-	20	-	dB	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,						
$Z_{\rm L} = Z_{\rm Lopt}$, $f = 1.8$ GHz						
Power gain, maximum available ¹⁾	G _{ma}	-	14.5	-	dB	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,						
$Z_{L} = Z_{Lopt}$, $f = 3 \text{ GHz}$						
Transducer gain	$ S_{21e} ^2$				dB	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω , f = 1.8GHz		15.5	18	-		
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω , f = 3GHz		-	13	-		
Third order intercept point at output ²⁾	IP3	_	24.5	_	dBm	
$V_{\rm CE}$ = 2 V, $I_{\rm C}$ = 20 mA, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω , f = 1.8GHz						
1dB compression point at output	P _{-1dB}	-	11	-		
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω , f = 1.8GHz						

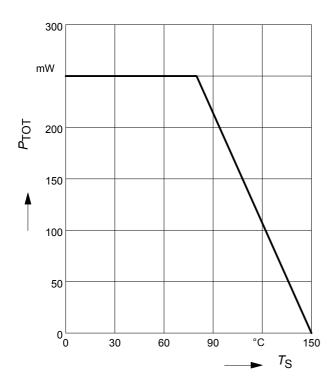
 $^{^{1}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2}), G_{\text{ms}} = |S_{21e} / S_{12e}|$

 $^{^2\}mbox{IP3}$ value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz



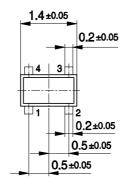
Total power dissipation $P_{tot} = f(T_S)$

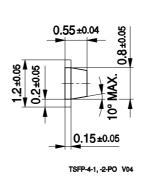




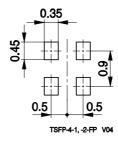
Package Outline



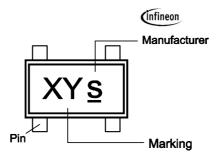




Foot Print

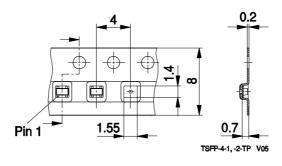


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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